

MBRS140T3

Preferred Device

Surface Mount Schottky Power Rectifier

Schottky Power Rectifiers employ the use of the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system.

Features

- Small Compact Surface Mountable Package with J-Bend Leads
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- Very Low Forward Voltage Drop
(0.55 V Max @ 1.0 A, $T_J = 25^\circ\text{C}$)
- Excellent Ability to Withstand Reverse Avalanche Energy Transients
- Guardring for Stress Protection
- Pb-Free Package is Available

Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 95 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes:
260°C Max. for 10 Seconds
- Cathode Polarity Band

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	40	V
Average Rectified Forward Current $T_L = 115^\circ\text{C}$	$I_{F(AV)}$	1.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	40	A
Operating Junction Temperature	T_J	-65 to +125	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



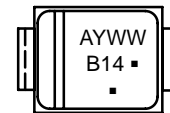
ON Semiconductor®

SCHOTTKY BARRIER RECTIFIER 1.0 AMPERE, 40 VOLTS



SMB
CASE 403A
PLASTIC

MARKING DIAGRAM



B14 = Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MBRS140T3	SMB	2500/Tape & Reel
MBRS140T3G	SMB (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MBRS140T3

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance – Junction-to-Lead ($T_L = 25^\circ\text{C}$)	$R_{\theta JL}$	12	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 1) ($i_F = 1.0\text{ A}$, $T_J = 25^\circ\text{C}$)	V_F	0.6	V
Maximum Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 100^\circ\text{C}$)	i_R	1.0 10	mA

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

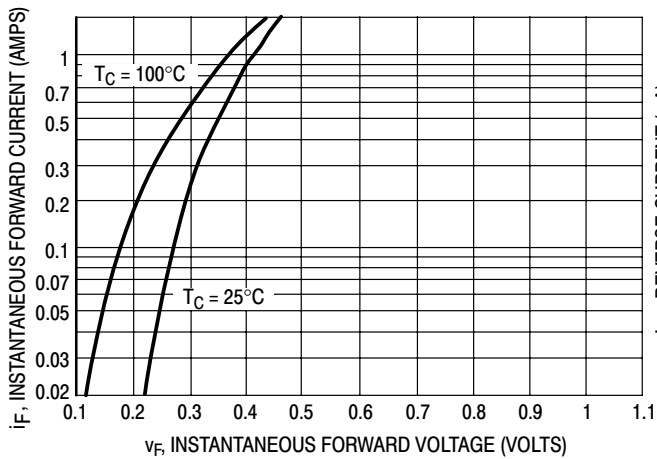


Figure 1. Typical Forward Voltage

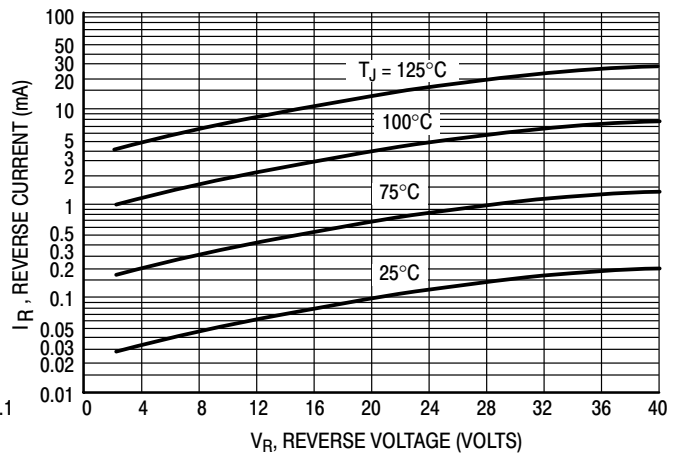
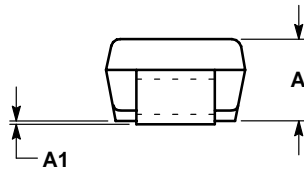
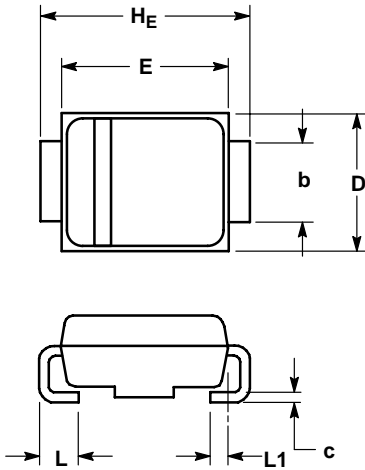


Figure 2. Typical Reverse Current

MBRS140T3

PACKAGE DIMENSIONS

SMB
CASE 403A-03
ISSUE F

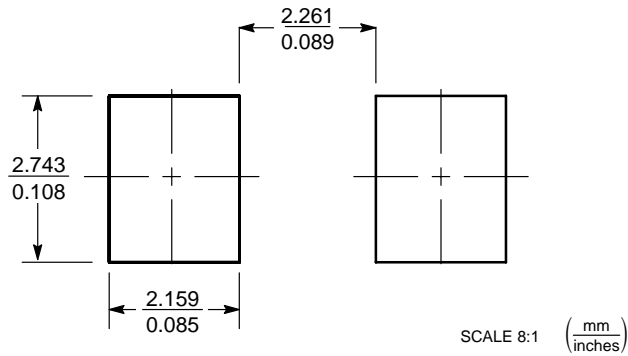


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.90	2.13	2.45	0.075	0.084	0.096
A1	0.05	0.10	0.20	0.002	0.004	0.008
b	1.96	2.03	2.20	0.077	0.080	0.087
c	0.15	0.23	0.31	0.006	0.009	0.012
D	3.30	3.56	3.95	0.130	0.140	0.156
E	4.06	4.32	4.60	0.160	0.170	0.181
H_E	5.21	5.44	5.60	0.205	0.214	0.220
L	0.76	1.02	1.60	0.030	0.040	0.063
L1	0.51 REF			0.020 REF		

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.